The 1st Japan-China Joint Workshop on Material Science in Space

(Supported by Research Institute of Electronics, Shizuoka University, Japan Aerospace Exploration Agency, and Chinese Academy of Sciences)

Date: February 9th
Place: Meeting Room (2nd Floor) of the Research Institute of Electronics, Shizuoka University
       3-5-1, Johoku, Naka-ku, Hamamatsu 432-8011, JAPAN

Chairman J. Yu
10:00 - 10:05 Opening Remarks
   Y. Hayakawa (Research Institute of Electronics, Shizuoka Univ.)

10:05 - 10:45 JAXA's Crystal Growth Experiments on ISS
   Y. Inatomi (ISAS, JAXA)

10:45 - 11:20 Introduction of Material Research in Shanghai Institute of Ceramics, CAS
   C. Zhong and Y. Liu (Shanghai Institute of Ceramics, CAS)

11:20 - 12:00 Introduction of Microgravity Experiments
   Y. Hayakawa (Research Institute of Electronics, Shizuoka Univ.)

12:00 - 13:30 Lunch

Chairman Y. Inatomi
13:30 - 13:55 Ground-based Experiments for Crystal Growth of InGaSb
   V. Nirmal Kumar, Y. Katsumata, M. Arivanandhan, T. Koyama, Y. Momose,
   Y. Hayakawa (Research Institute of Electronics, Shizuoka Univ.),
   Y. Okano (Osaka Univ.), T. Ozawa (Shizuoka Institute of Science and Technology),
   and Y. Inatomi (ISAS, JAXA)

13:55 - 14:20 Numerical Simulation of InGaSb Crystal Growth
   H. Mirsand and Y. Okano (Osaka Univ.)

14:20 - 14:45 Solidification and Crystal Growth Experiments in the SJ10-recoverable Scientific
   Experiment Satellite.
   X. Zhang (Institute of Semiconductors, CAS)

14:45 - 15:10 Development of Gradient Heating Furnace for the SJ10-recoverable Scientific
   Experiment Satellite.
   H. Pan and H. Zhao (Shanghai Institute of Ceramics, CAS)

15:10 - 15:20 Closing Remarks
   Y. Liu (Shanghai Institute of Ceramics, CAS)

15:20 - 16:00 Laboratory Tour at Glass Manufacturing Room and Hayakawa laboratory
   Y. Momose and Y. Hayakawa et al. (Research Institute of Electronics, Shizuoka Univ.)